Preparation of $\text{Si}_2\text{N}_2\text{O}$ from Flashing Combustion Synthesized $\text{Si}_3\text{N}_4$ and Silica Fume

B. Li$^1$, J.H. Chen$^{1*}$, M.W. Yan$^1$, X.P. Li$^1$, J.L. Sun$^1$ & Y. Li$^1$, M. Wei$^2$

$^1$School of Materials Science Engineering, University of Science and Technology Beijing, Beijing, P.R.China

$^2$Shanxi Jiangyang Chemical Co., Ltd., Taiyuan, P.R.China

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Abstract. Using flashing combustion synthesized $\text{Si}_3\text{N}_4$ and silica fume as raw materials, the effects of firing temperature (1300°C, 1400°C, 1500°C, and 1600°C) and duration (3h, 6h, and 9h) on the synthesis of $\text{Si}_2\text{N}_2\text{O}$ were studied. The results show that the main mechanism of the reaction is $\text{Si}_3\text{N}_4$ and silica fume react to form $\text{Si}_2\text{N}_2\text{O}$ through solid-solid reaction or solid-liquid reaction. After heat treatment at 1300°C, there is a small amount of melting liquid in the system, with a trace of $\text{Si}_2\text{N}_2\text{O}$ formed. After heat treatment at 1400°C, 1500°C, and 1600°C, there is a large amount of melting liquid in the system, accelerating the formation of $\text{Si}_2\text{N}_2\text{O}$ slightly. The duration has very little effect on the synthesis reaction. When $\text{Si}_2\text{N}_2\text{O}$ forms, the oxygen content in the melting liquid decreases, viscosity of the liquid increases, the diffusion of ions in the melting liquid slows, hindering the continuous crystallization of $\text{Si}_2\text{N}_2\text{O}$. Thus, a fusing agent or hot pressing is required to introduce more low viscosity liquid for the continuous crystallization of $\text{Si}_2\text{N}_2\text{O}$. In addition, silica fume crystallizes obviously at 1300°C and 1400°C.

Introduction

$\text{Si}_2\text{N}_2\text{O}$ is a ceramic material with high refractoriness featured with high thermodynamic stable temperature$^{[7]}$, excellent thermal shock resistance$^{[9]}$, good oxidation resistance, high hot strength, and good resistance to nonferrous metals melts$^{[1]}$, etc. Compared with $\text{Si}_3\text{N}_4$ ceramics it has better oxidation resistance at elevated temperatures, i.e. good oxidation resistance at 1600°C in air and high modulus of rupture at 1400°C$^{[6]}$. Therefore, $\text{Si}_2\text{N}_2\text{O}$ is a promising high temperature structural material used in high temperature oxidation condition.

$\text{Si}_2\text{N}_2\text{O}$ can be obtained by two approaches. The first one, use metal silicon and $\text{SiO}_2$ as starting materials, utilize the heat released by the SHS process to synthesize $\text{Si}_2\text{N}_2\text{O}$ in nitrogen atmosphere at high temperatures$^{[10]}$. The second one, use $\text{SiO}_2$ and $\text{Si}_3\text{N}_4$ as the starting materials to synthesize $\text{Si}_2\text{N}_2\text{O}$$^{[8]}$. $\text{Si}_2\text{N}_2\text{O}$ mainly forms from nitrogen containing liquid$^{[5]}$. In the second approach, the suitable liquid to produce $\text{Si}_2\text{N}_2\text{O}$ is the key point. What’s more, the reaction rate is very low. Thus, the preparation of $\text{Si}_2\text{N}_2\text{O}$ in China mainly adopts the first one and most of them are in lab-scale.

The efficiency of synthesis $\text{Si}_2\text{N}_2\text{O}$ from metal silicon is high, but the synthesis is directly influenced by factors such as the diffusion depth of nitrogen in the reaction system and the diffusion efficiency. In addition, the structure of the as-prepared products is hard to control. So this method is more suitable to synthesize $\text{Si}_2\text{N}_2\text{O}$ raw material. The preparation of $\text{Si}_2\text{N}_2\text{O}$ products requires methods such as hot pressed sintering based on the pre-synthesized starting materials$^{[4]}$.

As for the mass produced large sized products such as refractories, the SHS process of metal silicon greatly restrains the production of $\text{Si}_2\text{N}_2\text{O}$-related refractories. Take the penetration depth of nitrogen into the product bodies for example, commonly, the penetration depth of nitrogen in refractories is 3—4cm, too shallow for the blocks with thickness of dozens of centimeters. Besides, the process shall proceed in conditions of high temperature, high pressure and nitrogen atmosphere, which is hard to realize the industrialization.

Thus, in this work, $\text{Si}_2\text{N}_2\text{O}$ was prepared with silica fume and $\text{Si}_3\text{N}_4$ as raw materials sintered under normal pressure in hot carbon reduced air atmosphere, which is easy to industrialize. The silica fume was from the ferroalloy industry and has a high specific surface area and a high activity.
The Si\textsubscript{3}N\textsubscript{4} was prepared by flashing combustion method. The feasibility to industrialize this simple process was discussed. The effects of reaction temperature and duration on the synthesis of Si\textsubscript{2}N\textsubscript{2}O from silica fume and Si\textsubscript{3}N\textsubscript{4} were studied.

**Experiment**

The flashing combustion synthesized β-Si\textsubscript{3}N\textsubscript{4} fines with \(d_{50}\) of 45\,\mu m, and the silica fume with a SiO\textsubscript{2} content over 90\% and \(d_{50}\) of 0.85\,\mu m were adopted as the raw materials. Mixture with a Si\textsubscript{3}N\textsubscript{4} : SiO\textsubscript{2} mass ratio of 50\% : 50\% was ball mixed in a ball mill for 4h, adding with 0.2\% sodium hexametaphosphate. After drying, the ball-milled mixture was added with a temporary binder and pressed into specimens with sizes of Φ25×20mm under 6MPa.

As seen in the S-C-N-O system state diagram (Fig. 1), the dashed line corresponds to the hot carbon reduced air atmosphere. It is found that the stable phase at the temperature range of 1250—1700°C is Si\textsubscript{2}N\textsubscript{2}O, indicating this atmosphere is favorable to the formation of Si\textsubscript{2}N\textsubscript{2}O.

![State diagram of S-C-N-O system](image)

Figure 1. State diagram of S-C-N-O system

This work adopted the hot carbon reduced air atmosphere mentioned in Fig. 1. Blow the air slowly into a high temperature atmosphere furnace through a hot carbon net of 1500°C. Then, raise the temperature slowly to 1300°C, 1400°C, 1500°C, and 1600°C for duration of 3h, 6h, and 9h, respectively. Sample from the inside of the specimen and analyze with XRD (X’ pert PRO MPD, Philips, Netherlands), SEM (FEI Nova 230 Nano SEM, FEI Company, USA), and EDS (Inca Energy, Oxford, UK) to investigate the phase composition, microstructure, and element distribution of the specimens.

**Results and discussion**

1.1 *Experiment results*

(1)SEM analysis of raw materials

As can be seen in Fig. 2(a), the particles of silica fume from the ferroalloys industry are small, ranging from dozens to hundreds of nanometers. The flashing combustion synthesized silica nitride particles develop well with prismatic shapes. And the crystals interlock with each other with diameters of micrometers and length of dozens of micrometers.
(2) Analysis of specimens with different firing temperatures and different duration

① XRD analysis of specimens fired at 1300°C, 1400°C, 1500°C and 1600°C for 3h

As shown in Fig. 3, after firing at 1300°C, the peaks of Si$_2$N$_2$O are observed, indicating that Si$_2$N$_2$O forms at this temperature. As firing temperature rises, the peaks get stronger. After firing at 1600°C, the peaks of Si$_2$N$_2$O are very obvious. But in general, with the duration of 3h, the effect of firing temperature on the peaks is not obvious: the peak intensity gets stronger mildly as temperature rises. β-Si$_3$N$_4$ is still the main phase, meanwhile, SiO$_2$ is also a main phase, and the peaks of SiO$_2$ tend to be stronger at 1300～1400°C, after 1500°C the SiO$_2$ peaks weaken greatly, which means that the silica fume crystallizes intensely at 1300～1400°C. After 1500°C, the peaks get lower, and amorphous peaks appear at low angles in XRD patterns.

![Figure 3. XRD patterns of specimens fired at 1300°C, 1400°C, 1500°C and 1600°C for 3h](image)

② XRD analysis of specimens fired at 1300°C, 1400°C, 1500°C and 1600°C for 3h, 6h and 9h, respectively

As shown in Fig. 4, at firing temperature of 1300°C, the duration of 3h, 6h, 9h has no obvious influence on the peak intensity of Si$_2$N$_2$O. The peak intensities at firing temperature of 1400°C, 1500°C and 1600°C are stronger than that at 1300°C. However, at different temperatures, the duration has no influence on the crystallization of the Si$_2$N$_2$O. It is noted that the system has strong
SiO$_2$ peaks at 1300°C and 1400°C, which means that the crystallization force of the silica fume is very strong at the temperatures. At 1500°C and 1600°C, the peak intensity of SiO$_2$ decreases greatly and the XRD results show the appearance of amorphous phases, indicating that silica fume is in melting state. Peak intensity of $\beta$-Si$_3$N$_4$ varies slightly at different temperatures, meaning that the content of $\beta$-Si$_3$N$_4$ merely changes and proving it is stable in the system.

Fig. 4 XRD pattern of specimens fired at different sintering temperatures for different duration: (a) 1300°C; (b) 1400°C; (c) 1500°C; (d) 1600°C.

(3) SEM analysis of specimens fired at different temperatures for 6h

SEM photographs of specimens fired at different temperatures for 6h are shown in Fig.5. Combined with the XRD results, it is concluded that at 1300°C, only a small amount of melting phase forms in the system, and the Si$_2$N$_2$O formation is very little. Since there are some impurities existing in silica fume, a trace of melting liquid forms, resulting in some local closure and separation in the system. At 1300°C, most Si$_3$N$_4$ particles are loose and insolated. Small and uniform pores distributes among the particles. At 1400°C, the Si$_3$N$_4$ particles are still insolated, but some liquid phases appear in the system. Although the bonding is not strong, obvious packing and cementation exist. At 1500°C and 1600°C, the system is almost in melting state, with a totally closed state. Most Si$_3$N$_4$ particles are bonded together, few Si$_3$N$_4$ particles are insolated. Melting phases pack the Si$_3$N$_4$ particles tightly. With temperature increasing, the pores are becoming more and more and the pore volume increases. The whole system presents a cemented network structure.
1.2 Analysis and discussion

(1) Thermodynamics analysis of Si$_3$N$_4$—silica fume system

In this system, the formed Si$_2$N$_2$O is mainly from the following reactions.

\[
\text{Si}_3\text{N}_4(\text{s}) + \frac{3}{2}\text{CO}(\text{g}) = \frac{3}{2}\text{Si}_2\text{N}_2\text{O} + \frac{1}{2}\text{N}_2 + \frac{3}{2}\text{C} \quad (1)
\]

\[
\Delta_rG^0 = -381420.75 + 159.50T \text{ (J/mmol)}
\]

\[
\text{Si}_3\text{N}_4(\text{s}) + \frac{3}{4}\text{O}_2(\text{g}) = \frac{3}{2}\text{Si}_2\text{N}_2\text{O} + \frac{1}{2}\text{N}_2(\text{g}) \quad (2)
\]

\[
\Delta_rG^0 = -553023.50 + 30.85T \text{ (J/mmol)}
\]

\[
\text{Si}_3\text{N}_4(\text{s}) + \text{SiO}_2(\text{s}) = 2\text{Si}_2\text{N}_2\text{O}(\text{s}) \quad (3)
\]

\[
\Delta_rG^0 = -178770.00 + 31.10T \text{ (J/mmol)}
\]

As shown in Fig. 6, in normal conditions, reactions (1)–(3) can happen. Reaction (2) has the lowest $\Delta_rG^0$, making it the easiest one to happen. However, after 1400°C, the impurities in the silica fume form phases with low melting temperatures, blocking the pores and hindering the penetration of O$_2$ and CO, making the gas reactions hard to proceed in the system. Thus, the formation of
Si$_2$N$_2$O at different temperatures is based on the reaction between Si$_3$N$_4$ and silica fume. Reactions (1) and (2) are restrained in this system, therefore, the forming speed of Si$_2$N$_2$O depends on the speed of solid-solid reactions or solid-liquid reactions$^2$.

As shown in Fig. 6, in normal conditions, reactions (1) – (3) can happen. Reaction (2) has the lowest $\Delta_rG^\theta$, making it the easiest one to happen. However, after 1400°C, the impurities in the silica fume form phases with low melting temperatures, blocking the pores and hindering the penetration of O$_2$ and CO, making the gas reactions hard to proceed in the system. Thus, the formation of Si$_2$N$_2$O at different temperatures is based on the reaction between Si$_3$N$_4$ and silica fume. Reactions (1) and (2) are restrained in this system, therefore, the forming speed of Si$_2$N$_2$O depends on the speed of solid-solid reactions or solid-liquid reactions$^2$.

(2) Effect of temperature on Si$_2$N$_2$O crystallization

Diffusion between solid SiO$_2$ and Si$_3$N$_4$ is slow. If only relying on the contact diffusion between the two solids, there will be only very a small amount of Si$_2$N$_2$O forming. The growth of Si$_2$N$_2$O crystals just likes the synthesis of Stalon: as the appearance of liquid, Si$_2$N$_2$O crystallizes from the liquid, and grows bigger. So the liquid in the system is a key factor to make the Si$_2$N$_2$O crystals nucleate and grow. Therefore, a large amount of Si-N-O-X silicate melting phase is the necessary condition to form Si$_2$N$_2$O.

After firing at 1300°C, only a trace of melting liquid forms in the system (Fig. 5(a)), Si$_2$N$_2$O can only be formed by the diffusion or through the very limited liquid, so very little Si$_2$N$_2$O forms. As temperature rises, the liquid is becoming more and more: liquid is not obvious at 1300°C, but obvious at 1400°C; at 1500°C and 1600°C, the system melts completely. However, as temperature increases, the Si$_2$N$_2$O peaks tend to be obvious, but the increase is slight, and there is no large amount of Si$_2$N$_2$O formed. The increase of temperature enhances the liquid content of the system but only slightly improves the crystallization of Si$_2$N$_2$O.

(3) Effect of duration on Si$_2$N$_2$O crystallization

The XRD patterns of specimens fired at one temperature for different duration (Fig. 4) show that at 1300°C, 1400°C, 1500°C, and 1600°C, with duration increasing from 3h to 9h, the diffraction peaks of Si$_2$N$_2$O do not increase obviously, indicating the system does not have a large amount of Si$_2$N$_2$O formed. At 1500°C and 1600°C, the melting liquid content in the system is relatively high. In this condition, prolonging the duration has no accelerating effect on Si$_2$N$_2$O crystallization.

(4) Analysis on Si$_2$N$_2$O crystallization mechanism in Si$_3$N$_4$ – silica fume system

At 1300°C and 1400°C, strong silica fume crystallization appears in the system. The structure of short-range order and long-range disorder has turned into long-range order structure. Some Si-Si and O-O bonds break, forming a stable tetrahedral structure with Si-O bonds. At 1500°C and 1600°C, silica fume melts, providing the precursor for the growth of Si$_2$N$_2$O crystals.

When solid or melting SiO$_2$ contacts with the surface of Si$_3$N$_4$ crystals, some [Si-N] tetrahedrons or groups leave the surface of Si$_3$N$_4$ crystals and diffuse into the melt. [Si-N] tetrahedrons or groups react with O$^-$ or [Si-O] tetrahedrons from the melt, breaking Si-N bonds and establishing new Si-O bonds, so Si$_2$N$_2$O crystallizes. Once Si$_2$N$_2$O crystals form, the oxygen content in the melt declines and the liquid viscosity increases, making ions in the melt hard to diffuse and thus hindering the continuous crystallization of Si$_2$N$_2$O. Therefore, for the continuous crystallization of Si$_2$N$_2$O, a fusing agent or hot pressing is required$^{11, 5}$, because this will introduce more low viscosity liquid for the mass crystallization of Si$_2$N$_2$O.

Conclusions

(1) In reduction atmosphere, Si$_2$N$_2$O was synthesized using flashing combustion synthesized Si$_3$N$_4$ and silica fume as raw materials. Because of the self-close effect of silica fume, the Si$_2$N$_2$O phase is the direct reaction product of Si$_3$N$_4$ and silica fume.

(2) After heat treatment at 1300°C, there is a small amount of melting liquid in the system, with a trace Si$_2$N$_2$O formed. After heat treatment at 1400°C, 1500°C, and 1600°C, there is a large amount of melting liquid in the system, accelerating the formation of Si$_2$N$_2$O slightly. The temperature
rising can enhance the melt content of the system, but only slightly improves the Si$_2$N$_2$O crystallization. The prolonging of duration has very little effect on the Si$_2$N$_2$O crystallization.

(3) The system show strong silica fume crystallization at 1300°C and 1400°C. At 1500°C and 1600°C, the silica fume is melting and amorphous.

(4) When Si$_2$N$_2$O crystals form, the oxygen content in the melting liquid decreases, liquid viscosity increases as well, so the diffusion of ions in the melt becomes difficult, hindering the continuous crystallization of Si$_2$N$_2$O. Thus, fusing agent or hot press is required to introduce more low viscosity liquid for the continuous crystallization of Si$_2$N$_2$O.

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